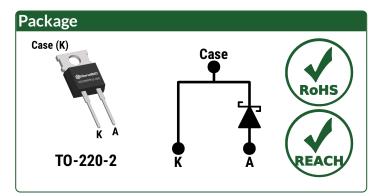
Silicon Carbide Schottky Diode



 V_{RRM} = 1200 V $I_{F(T_C = 164^{\circ}C)}$ = 2 A Q_C = 11 nC

Features

- Low V_F for High Temperature Operation
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Qc/IF
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V_F
- High dV/dt Ruggedness



Advantages

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

Applications

- High Voltage Sensing
- Solar Inverters
- Electric Vehicles
- High Frequency Converters
- Battery Chargers
- AC/DC Power Supplies
- Anti-Parallel / Free-Wheeling Diode
- LED and HID Lighting

Absolute Maximum Ratings (At T _C = 25°C Unless Otherwise Stated)								
Parameter	Symbol	Conditions	Values	Unit	Note			
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V				
	l _F	$T_C = 100^{\circ}C$, D = 1	6					
Continuous Forward Current		$T_C = 135^{\circ}C$, D = 1	4	Α	Fig. 4			
		$T_C = 164^{\circ}C, D = 1$	2					
Non-Repetitive Peak Forward Surge Current, Half Sine	lea	T_C = 25°C, t_P = 10 ms	20	۸				
Wave	I _{F,SM}	T_C = 150°C, t_P = 10 ms	16	Α				
Repetitive Peak Forward Surge Current, Half Sine Wave		$T_{C} = 25^{\circ}\text{C}, t_{P} = 10 \text{ ms}$		12	٨			
	IF,RM	T_C = 150°C, t_P = 10 ms	8	Α				
Non-Repetitive Peak Forward Surge Current	I _{F,MAX}	T_C = 25°C, t_P = 10 μ s	100	Α				
i ² t Value	∫i²dt	T_C = 25°C, t_P = 10 ms	2.0	A ² s				
Non-Repetitive Avalanche Energy	E _{AS}	L = 18.0 mH, I _{AS} = 2 A	36	mJ				
Diode Ruggedness	dV/dt	$V_R = 0 \sim 960 \text{ V}$	200	V/ns				
Power Dissipation	P _{TOT}	T _C = 25°C	54	W	Fig. 3			
Operating and Storage Temperature	T_j , T_{stg}		-55 to 175	°C				



Electrical Characteristics	;							
Parameter	Symbol	Conditions		Values			Unit	Note
	Зушьог			Min.	Тур.	Max.	Ullit	Note
Diode Forward Voltage	V_{F}	$I_F = 2 A, T_j = 25^{\circ}C$			1.5	1.8	٧	Fig. 1
	VF	$I_F = 2 A, T_j = 175^{\circ}C$			1.9			
Reverse Current	l _n	V _R = 1200 V, T _j = 25°C			1	5	μΑ	Fig. 2
	IR	$V_R = 1200 \text{ V, } T_j = 175^{\circ}\text{C}$			3			
Total Capacitive Charge	Qc		V_R = 400 V		7		nC	Fig. 7
	Q U	I _F ≤ I _{F,MAX}	$V_R = 800 V$		11		110	
Switching Time	ts	$dI_F/dt = 200 A/\mu s$	V_R = 400 V		< 10		ns	
	ις		$V_{R} = 800 V$		\ 10		113	
Total Capacitance	С	$V_R = 1 V, f = 1MHz$			122		ьE	Fig. 6
		V _R = 800 V, f = 1MHz			7		pF 	

Thermal/Package Characteristics							
Parameter	Symbol	Conditions	Values			Heit	Note
		Conditions	Min.	Тур.	Max.	- Unit	Note
Thermal Resistance, Junction - Case	R_{thJC}			2.79		°C/W	Fig. 9
Weight	W _T			2.0		g	
Mounting Torque	T _M	Screws to Heatsink			1.0	Nm	





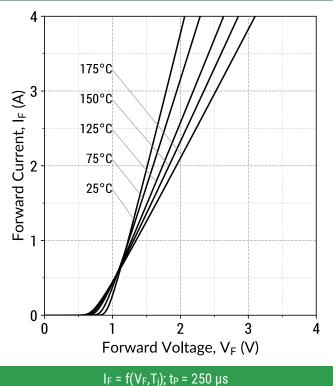


Figure 2: Typical Reverse Characteristics

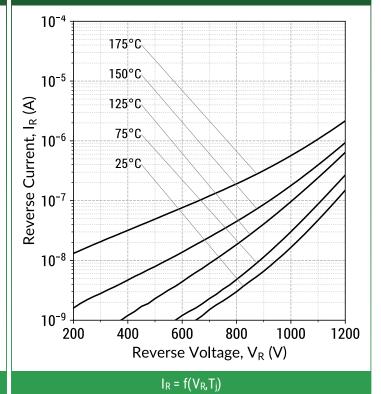


Figure 3: Power Derating Curves

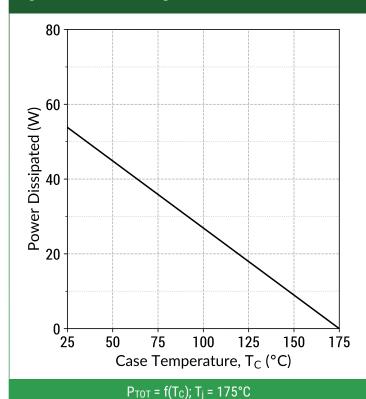
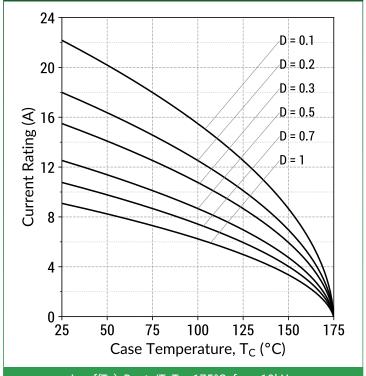


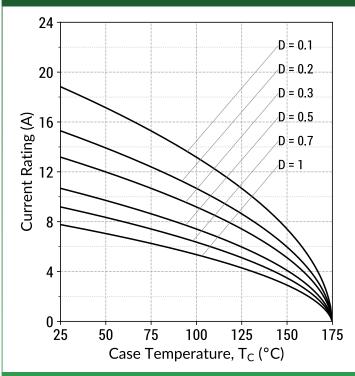
Figure 4: Current Derating Curves (Typical V_F)



 $I_F = f(T_C); D = t_P/T; T_j \le 175^{\circ}C; f_{SW} > 10kHz$

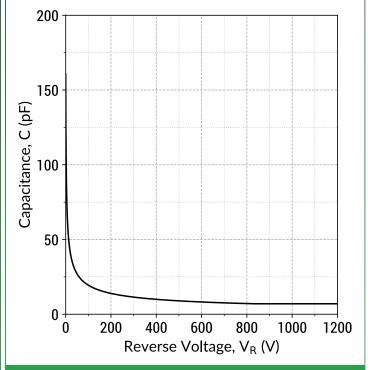


Figure 5: Current Derating Curves (Maximum V_F)



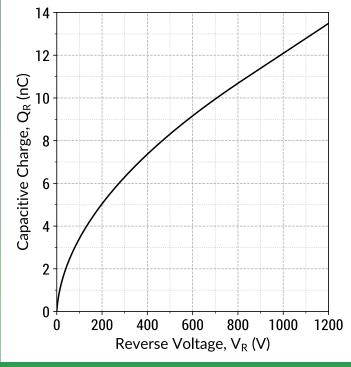
 $I_F = f(T_C)$; D = t_P/T ; $T_j \le 175$ °C; $f_{SW} > 10$ kHz

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics



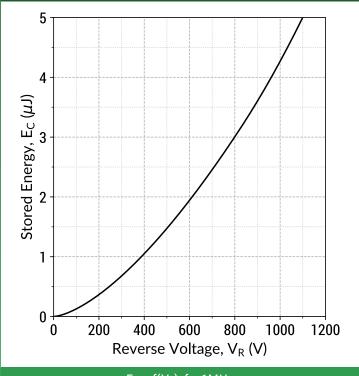
 $C = f(V_R)$; f = 1MHz

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics



 $Q_C = f(V_R)$; f = 1MHz

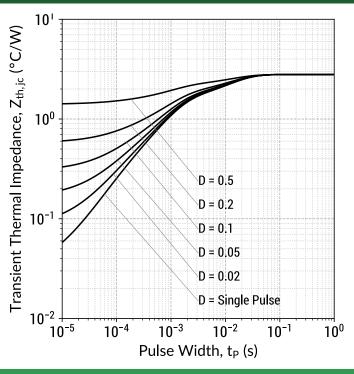
Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics



 $E_C = f(V_R)$; f = 1MHz

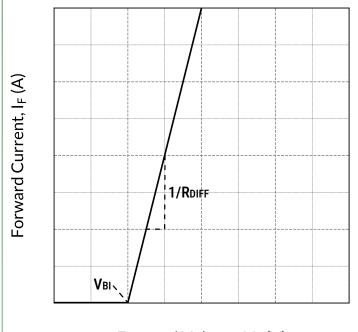


Figure 9: Transient Thermal Impedance



 $Z_{th,jc} = f(t_P,D); D = t_P/T$

Figure 10: Forward Curve Model



Forward Voltage, $V_F(V)$

 $I_F = f(V_F, T_j)$

Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF}(A)$

Built-In Voltage (V_{BI}):

$$V_{BI}(T_j) = m \times T_j + n (V)$$

 $m = -0.00123 (V/^{\circ}C)$
 $n = 0.995 (V)$

Differential Resistance (RDIFF):

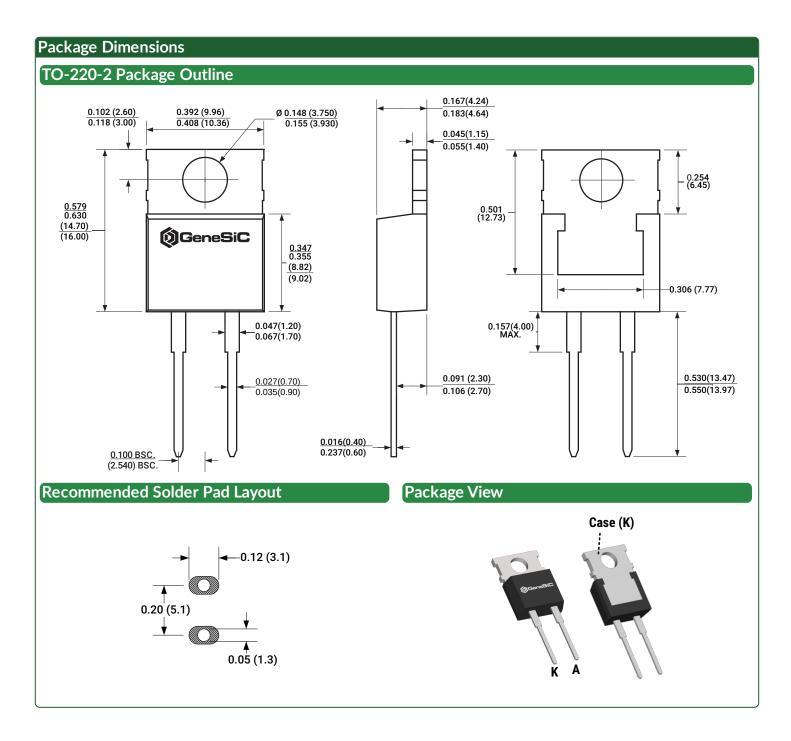
$$R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$$

 $a = 5.96e-06 (\Omega/^{\circ}C^2)$
 $b = 0.000846 (\Omega/^{\circ}C)$
 $c = 0.251 (\Omega)$

Forward Power Loss Equation:

$$P_{LOSS} = V_{BI}(T_i) \times I_{AVG} + R_{DIFF}(T_i) \times I_{RMS}^2$$





NOTE

- 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.





Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

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Revision History

Rev 21/Jul: Updated with most recent test data
Supersedes: Rev 19/Apr, Rev 20/Apr, Rev 20/Aug



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